

Publikationen

- (2011): Degradation of polycrystalline HfO₂ based gate dielectrics under nanoscale electrical stress. In: Applied Physics Letters, vol. 99.
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- (2011): Reliability and gate conduction variability of HfO₂-based MOS devices: A combined nanoscale and device level study. In: Microelectronic Engineering, vol. 88, pp. 1334-1337.
- (2011): Conductivity and Charge Trapping After Electrical Stress in Amorphous and Polycrystalline Al₂O₃-Based Devices Studied With AFM-Related Techniques. In: IEEE Transactions on Nanotechnology, vol. 10, no. 2, pp. 344-351.
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- (2007): Influence of the manufacturing process on the electrical properties of thin (< 4 nm) Hafnium based high-k stacks observed with CAFM. In: 18th European Symposium on Reliability of Electronic Devices, Failure Physics and Analysis (ESREF), Arcachon, Frankreich.
- (2007): Influence of the manufacturing process on the electrical properties of thin (< 4 nm) Hafnium based high-k stacks observed with CAFM. In: Microelectronics Reliability, vol. 47, no. 9, pp. 1424-1428.